

## General Description

The MDS1653 uses advanced MagnaChip's MOSFET Technology, which provides low on-state resistance, high switching performance and excellent reliability.

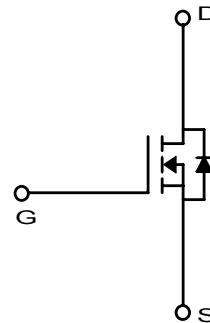
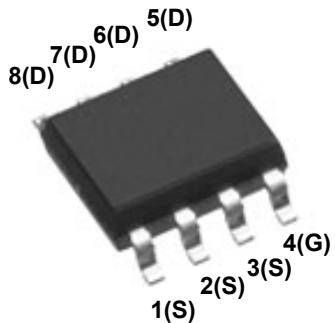
MDS1653 is suitable device for DC-DC Converters and general purpose applications.

## Features

- $V_{DS} = 30V$
- $I_D = 12A$  @  $V_{GS} = 10V$
- $R_{DS(ON)}$   
 $< 12.0m\Omega$  @  $V_{GS} = 10V$   
 $< 17.5m\Omega$  @  $V_{GS} = 4.5V$

## Applications

- DC-DC Converters



## Absolute Maximum Ratings ( $T_a = 25^\circ C$ )

Characteristics	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DSS}$	30	V
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Continuous Drain Current	$I_D$	12	A
$T_a=100^\circ C$		8.6	A
Pulsed Drain Current	$I_{DM}$	50	A
Power Dissipation <sup>(1)</sup>	$P_D$	2.5	W
$T_a=100^\circ C$		1.25	
Single Pulse Avalanche Energy <sup>(2)</sup>	$E_{AS}$	50	mJ
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55~150	°C

## Thermal Characteristics

Characteristics	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Ambient <sup>(1)</sup>	$R_{\theta JA}$	50	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	25	